

8-bit 200/300 MSPS Flash A/D Converter

Description

The CXA1076K/CXA1176K are monolithic flash A/D converters capable of digitizing 0 to -2V analog input signal into 8-bit binary code at a sampling rate of 200MSPS (CXA1076K)/300MSPS (CXA1176K).

They operate with a single -5.2V power supply and consume only 720/1300 mW.

The digital I/O level is compatible with 100K/10KH/10K series ECL, and complementary digital output makes ease to interface to external circuits. Output ports have a capability to drive into $50\ \Omega$ load to -2 V.

In addition to 8-bit output data, they have an over range output and two digital inputs which enable to program output format for true, inverse binary and offset two's complement.

Features

- Ultra high speed (CXA1076K) 200MSPS (CXA1176K) 300MSPS
- Wide input band width (CXA1076K) 1.1 MHz (CXA1176K) 1.5 MHz
- Low power consumption (CXA1076K) 720 mW (CXA1176K) 1300 mW
- Internal linearity better than 0.1% (CXA1076K)
- Complementary digital output
- Over range output
- Programmable output format
- Small 68 LCC package

Applications

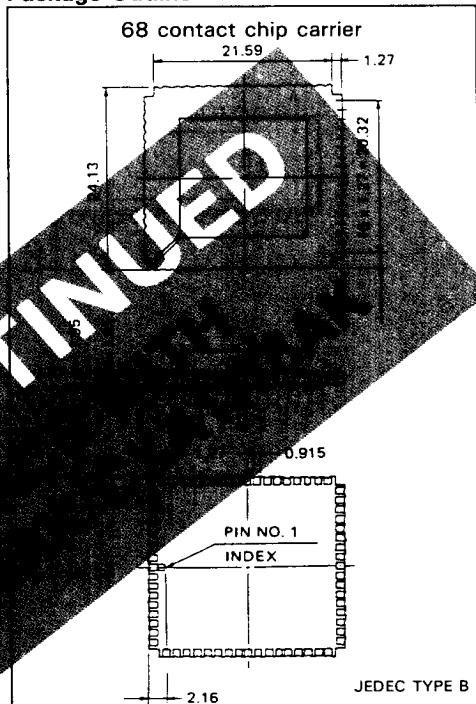
Digital oscilloscope, radar, spectrum analysis, transient capture and fast digital signal processing.

Absolute Maximum Ratings ($T = 25^\circ\text{C}$)

• Supply voltage	$\text{AV}_{\text{EE}}, \text{DV}_{\text{EE}}$	0.5 to -7	V
• Analog input voltage	V_{IN}	0.5 to V_{EE}	V
• Reference input voltage	$\text{V}_{\text{RT}}, \text{V}_{\text{RB}}$	0.5 to V_{EE}	V
	$\text{V}_{\text{RT}}-\text{V}_{\text{RB}}$	0 to 2.5	V
• Digital input voltage	$\text{CLK}, \overline{\text{CLK}}, \text{MINV}, \text{LINV}$	0.5 to V_{EE}	V
• Digital output current	IDO to $\text{ID7}, \text{IOR}$	0 to -30	mA
	$\overline{\text{IDO}}$ to $\overline{\text{ID7}}, \overline{\text{IOR}}$	0 to -30	mA
• Operating temperature	T_a	-25 to +75	$^\circ\text{C}$
	T_c	-55 to +125	$^\circ\text{C}$
• Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
• Allowable power dissipation	P_{D}	1.8	W

Package Outline

Unit: mm



SONY® CXA1076AK/CXA1176AK

8-bit 200/300 MSPS Flash A/D Converter

Advance
Information

Evaluation Board Available — CXA1076AK PCB/CXA1176AK PCB

Notice: This specification is subject to change.

Description

CXA1076AK/CXA1176AK are monolithic flash A/D converters capable of digitizing 0 to -2 V analog input signal into 8-bit binary code at a sampling rate of 200MSPS (CXA1076AK)/300MSPS (CXA1176AK).

They operate with a single -5.2 V power supply and consume only 1450 mW.

The digital I/O level is compatible with 100K/10KH/10K series ECL, and complementary digital output makes ease to interface to external circuits. Output ports have a capability to drive into $50\ \Omega$ load to -2 V.

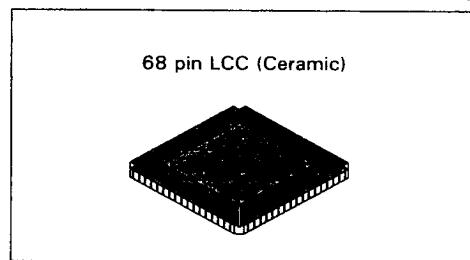
In addition to 8-bit output data, they have an over range output and two digital inputs which enable to program output format for true or inverse binary and offset two's complement.

Features

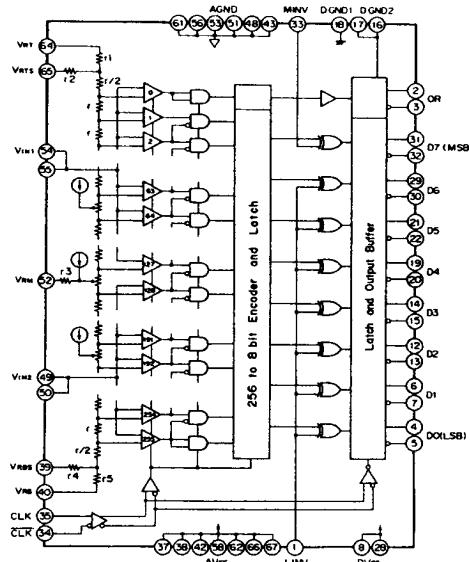
- Ultra high speed
- Wide input band width
- Low power consumption 1450 mW
- Internal linearity compensation circuit
- Complementary ECL output
- Over range output
- Programmable output format
- Small 68 LCC package
- Pin replacable with CXA1076K/CXA1176K

Applications

Digital oscilloscope, radar, image processing, transient capture and fast digital signal processing.



Block Diagram



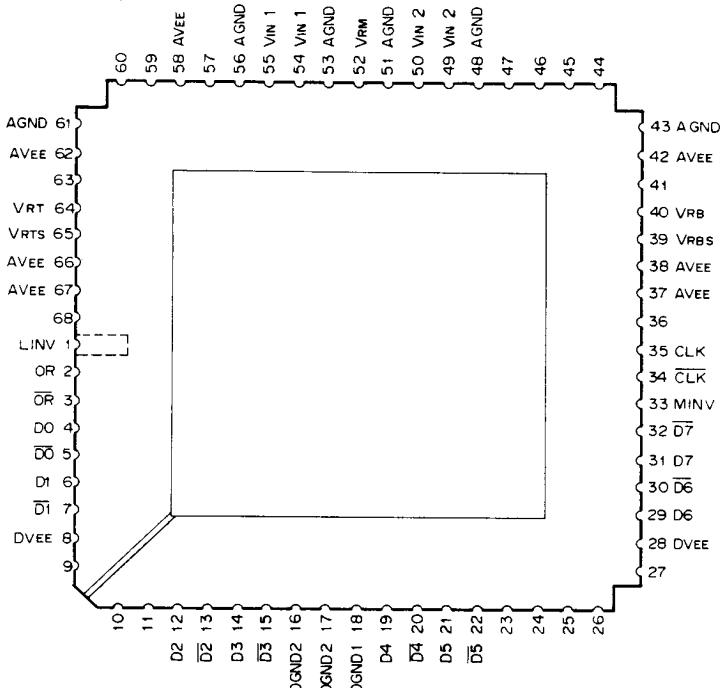
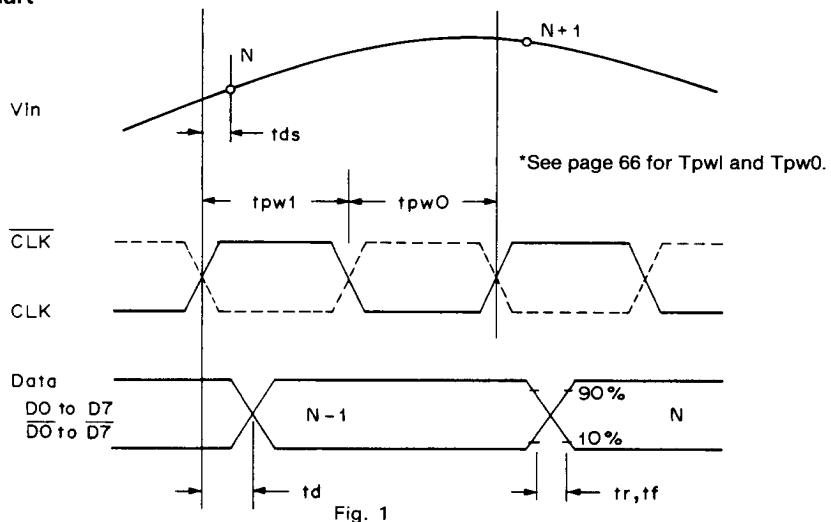
AE89670-YA

Absolute Maximum Ratings (Ta = 25°C)

• Supply voltage	AV_{EE} , DV_{EE}	0.5 to – 7	V
• Analog input voltage	V_{IN}	0.5 to V_{EE}	V
• Reference input voltage	V_{RT} , V_{RB}	0.5 to V_{EE}	V
	$V_{RT}-V_{RB}$	0 to 2.5	V
• Digital input voltage	CLK , \bar{CLK} , $MINV$, $LINV$	0.5 to V_{EE}	V
• Digital output current	ID_0 to ID_7 , IOR	0 to – 30	mA
	\overline{ID}_0 to \overline{ID}_7 , \overline{IOR}	0 to – 30	mA
• Operating temperature	T_a	– 25 to + 75	°C
	T_c	– 55 to + 125	°C
• Storage temperature	T_{stg}	– 65 to + 150	°C
• Allowable power dissipation	P_D	1.8	W

Recommended Operating Conditions

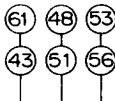
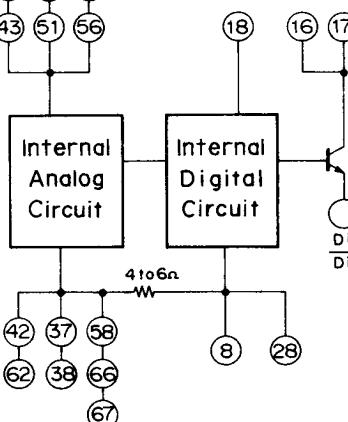
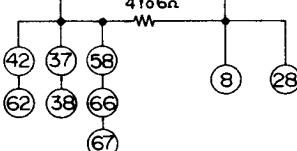
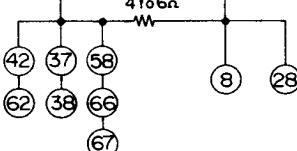
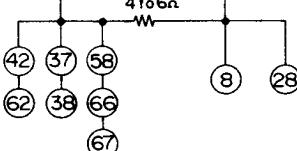
Item	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	AV_{EE} , DV_{EE}	– 4.95	– 5.2	– 5.5	V
Supply voltage	$AV_{EE} - DV_{EE}$		0	0.05	V
Ground	$DGND - AGND$		0	0.05	V
Analog input voltage	V_{IN}	V_{RB}		V_{RT}	
Reference input voltage	V_{RT}	– 0.1	0	+ 0.2	V
Reference input voltage	V_{RB}	– 2.2	– 2	– 1.9	V
Digital input voltage	V_{IH}	– 1.0		– 0.7	V
Digital input voltage	V_{IL}	– 1.9		– 1.6	V
Clock pulse width	TPW1 (CXA1076AK)	3.5			ns
Clock pulse width	TPW0 (CXA1076AK)	1.5			ns
Clock pulse width	TPW1 (CXA1176AK)	2.5			ns
Clock pulse width	TPW0 (CXA1176AK)	0.8			ns

Pin Configuration (Top View)**Timing Chart**

Pin Description and I/O Equivalent Circuits

No.	Symbol	Equivalent circuit	Description
4 5	D ₀ \overline{D}_0	<p>This diagram shows the internal logic for the first 14 pins. It includes a differential input stage with transistors and resistors, followed by a driver stage with a p-channel MOSFET and an n-channel MOSFET. The outputs are labeled D_i and \overline{D}_i. Pin 18 is connected to DGND1. Pin 16 is connected to DGND2. Pin 17 is connected to DV_{EE}. Pin 8 is connected to DV_{EE}.</p>	LSB and complementary LSB output
6 7	D ₁ \overline{D}_1		D ₁ to D ₆ : output \overline{D}_1 to \overline{D}_6 : complementary output
12 13	D ₂ \overline{D}_2		
14 15	D ₃ \overline{D}_3		
19 20	D ₄ \overline{D}_4		
21 22	D ₅ \overline{D}_5		
29 30	D ₆ \overline{D}_6		
31 32	D ₇ \overline{D}_7		MSB and complementary MSB output
2 3	OR \overline{OR}		Over Range and complementary Over Range output
33	MINV	<p>This diagram shows the polarity select circuit for pin 33. It consists of a p-channel MOSFET and an n-channel MOSFET. The gate of the p-channel MOSFET is connected to pin 18 (DGND1) through a diode. The drain of the p-channel MOSFET is connected to the drain of the n-channel MOSFET. The source of the n-channel MOSFET is connected to DV_{EE}. The drain of the n-channel MOSFET is connected to the output terminal. A -1.3V reference voltage is also connected to the drain of the n-channel MOSFET.</p>	Polarity select for MSB (Refer to coding table) L level is maintained with left open.
1	LINV		Polarity select for LSBs (Refer to coding table) L level is maintained with left open.

No.	Symbol	Equivalent circuit	Description
35	CLK	DGND1 18	CLK input
34	CLK	CLK 35 34 8 28	Complementary CLK input V _{BB} (-1.3V) is maintained with left open. With bypassing, it can be used as a reference for single CLK input.
64	V _{RT}	V _{RT} 64 65 r ₂ r ₁	Analog reference voltage (Top) (0V Typ.)
65	V _{RTS}	V _{RTS} r ₂ /2 r _r	Reference voltage sense (Top)
52	V _{RM}	V _{RM} 25 r ₃ r _r r ₂ /2 To Comparators	Reference voltage mid-point It can be used as a linearity compensation.
39	V _{RBS}	V _{RBS} 39 r ₄ r _r r ₂ /2 r ₅	Reference voltage sense (Bottom)
40	V _{RB}	V _{RB} 40 49,51,53,56 AGND	Analog reference voltage (Bottom) (-2V Typ.)
49 50 54 55	V _{IN}	49 50 54 55 To Comp 128to255 0to127	Analog input All of the pins must be wired externally.

No.	Symbol	Equivalent circuit	Description
43, 48, 51, 53, 56, 61	AGND (*1)		Analog ground
37, 38, 42, 58, 62, 66, 67	AVEE (*1)		Analog supply
18	DGND1		Digital ground
16 17	DGND2 (*1)		Digital ground for output drive
8 28	DVEE (*1)		Digital supply
9, 10 11, 23 24, 25 26, 27 36, 68	NC		Empty pins It is recommended to wire these pins to DGND.
41, 44 45, 46 47, 57 59, 60 63	NC		Empty pins It is recommended to wire these pins to AGND.

(*1) All of these pins must be wired to the respective external circuit.

Input-Output Reference and Output Format

Vin	Step	MINV	1	0		1		0	
		LINV	1	1		0		0	
		OR	MSB	LSB	OR	MSB	LSB	OR	MSB
0V	0	0	0 0 0 0 · · 0 0	0 1 0 0 · · 0 0	0	0 1 1 1 · · 1 1	0	1 1 1 1 · · 1 1	
	1	1	0 0 0 0 · · 0 0	1 1 0 0 · · 0 0	1	0 1 1 1 · · 1 1	1	1 1 1 1 · · 1 1	
	
-1V	127	1	0 1 1 1 · · 1 1	1 1 1 1 · · 1 1	1	0 0 0 0 · · 0 0	1	1 0 0 0 · · 0 0	
	128	1	1 0 0 0 · · 0 0	1 0 0 0 · · 0 0	1	1 1 1 1 · · 1 1	1	0 1 1 1 · · 1 1	
	
	254	1	1 1 1 1 · · 1 0	1 0 1 1 · · 1 0	1	1 0 0 0 · · 0 1	1	0 0 0 0 · · 0 1	
-2V	255	1	1 1 1 1 · · 1 1	1 0 1 1 · · 1 1	1	1 1 0 0 · · 0 0	1	0 0 0 0 · · 0 0	
		1	1 1 1 1 · · 1 1	1 0 1 1 · · 1 1	1	1 1 0 0 · · 0 0	1	0 0 0 0 · · 0 0	

Table 1

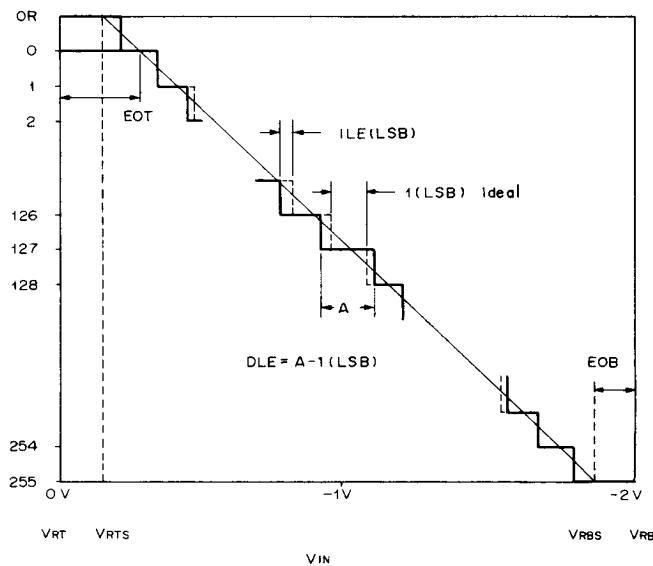


Fig. 2

Electrical Characteristics — CXA1076AK

$T_a = 25^\circ\text{C}$, $\text{AV}_{EE} = \text{DV}_{EE} = -5.2\text{ V}$
 $\text{VRT} = \text{VRTS} = \text{OV}$, $\text{VRB} = \text{VRBS} = -2\text{ V}$

Notice: Some parameter specs are subject to change.

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Maximum conversion rate (1)	F _C	V _{IN} = F _S , F _{IN} = 1 kHz	200	240		MSPS
Maximum conversion rate (2)	F _C	V _{IN} = F _S F _{IN} = 49.999 MHz	200	240		MSPS
Resolution				8		bit
Integral linearity	E _{IL}	F _C = 200 MSPS		±0.3	±0.5	LSB
Differential linearity	E _{DL}			±0.3	±0.5	LSB
Offset error	V _{RT}		12.0	14.5	17.0	mV
	V _{RB}	E _{OB}		4.0	6.5	mV
Analog input capacitance	C _{IN}	V _{IN} = -1 V + 0.07 rms	21	25	35	pF
Analog input current	I _{IN}	V _{IN} = OV	70	150	700	µA
Supply current	Analogue	I _{EEA}		150	200	mA
	Digital	I _{EED}		60	70	mA
Reference resistance	R _{REF}	V _{RT} to V _{RB}	75	90	108	Ω
Residual resistance	r ₁ , r ₅		0.43	0.52	0.62	Ω
	r ₂ , r ₄		0.64	0.77	0.92	Ω
	r ₃		2.8	3.4	4.1	Ω
Input level digital	H	V _{IH}		-1.0	-0.85	V
	L	V _{IL}		-1.9	-1.75	V
Output level digital	H	V _{OH}	R _L = 50 Ω to -2 V FO = 1 (100 K ECL)	-1.05		V
	L	V _{OL}			-1.6	V
Output data delay	t _d		1.7	2.0	ns	
Rise time output digital	t _r		0.8	1.2	ns	
Fall time output digital	t _f		0.8	1.2	ns	
Full scale input BW (-3dB)	BW _F	V _{IN} = F _S (*1)		220		MHz
Small signal input BW	BW _s	V _{IN} = 0.6 Vp-p (*1)		TBD		MHz
Aperture jitter	t _{aj}			3.0	3.6	ps
Sampling delay	t _{ds}		0.6	0.8	1.1	ns
SNR1		F _{IN} = 1 MHz FS (*1) F _C = 200MSPS		-46	-45.5	dB
SNR2		F _{IN} = 80 MHz, 0.6 Vp-p F _C = 200MSPS (*1)		TBD		dB
Differential gain	DG	NTSC 40 IRE mod. ramp F _C = 200 MSPS			1.0	%
Differential phase	DP				0.5	deg.
Error rate	E _R	F _C = 200 MSPS F _{IN} = 49.999 MHz V _{IN} = 2 Vp-p tpw1 = 3.5 ns tpw0 = 1.5 ns Error Threshold: 32 LSB			10 ⁻⁸	times/ sample

(*1) Source impedance = 50 Ω.

Electrical Characteristics — CXA1176AK

$T_a = 25^\circ C$, $V_{EE} = DV_{EE} = -5.2 V$
 $V_{RT} = V_{RTS} = OV$, $V_{RB} = V_{RBS} = -2 V$

Notice: Some parameter specs are subject to change.

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Maximum conversion rate (1)	F _C	$V_{IN} = FS$, $F_{IN} = 1$ kHz	300	340		MSPS	
Maximum conversion rate (2)	F _C	$V_{IN} = FS$ $F_{IN} = 62.499$ MHz	250	290		MSPS	
Resolution				8		bit	
Integral linearity	E _{IL}	F _C = 300 MSPS		± 0.3	± 0.5	LSB	
Differential linearity	E _{DL}			± 0.3	± 0.5	LSB	
Offset error	V _{RT}		12.0	14.5	17.0	mV	
	V _{RB}	E _{OB}		4.0	6.5	mV	
Analog input capacitance	C _{IN}	$V_{IN} = -1$ V + 0.07 rms	21	25	35	pF	
Analog input current	I _{IN}	$V_{IN} = OV$	70	150	700	μA	
Supply current	Analog Digital	I _{EEA}		150	200	mA	
		I _{EED}		60	70	mA	
Referrence resistance	R _{REF}	V _{RT} to V _{RB}	75	90	108	Ω	
	r ₁ , r ₅		0.43	0.52	0.62	Ω	
Residual resistance	r ₂ , r ₄		0.64	0.77	0.92	Ω	
	r ₃		2.8	3.4	4.1	Ω	
Input level digital	H	V _{IH}		-1.0	-0.85	-0.7	V
	L	V _{IL}		-1.9	-1.75	-1.6	V
Output level digital	H	V _{OH}	R _L = 50 Ω to -2 V FO = 1 (100 K ECL)	-1.05			V
	L	V _{OL}				-1.6	V
Output data delay	t _d			1.7	2.0	3.1	ns
Rise time output digital	t _r			0.8	1.2	1.5	ns
Fall time output digital	t _f			0.8	1.2	1.5	ns
Full scale input BW (-3dB)	BW _F	$V_{IN} = FS$ (*2)		250			MHz
Small signal input BW	BW _S	$V_{IN} = 0.6$ Vp-p (*2)		TBD			MHz
Aperture jitter	t _{aj}				3.0	3.6	ps
Sampling delay	t _{ds}			0.6	0.8	1.1	ns
SNR1		F _{IN} = 1 MHz FS (*2) F _C = 300MSPS			-46	-45.5	dB
SNR2		F _{IN} = 80 MHz, 0.6 Vp-p F _C = 300MSPS (*2)		TBD			dB
Differential gain	DG	NTSC 40 IRE mod. ramp F _C = 300 MSPS				1.0	%
Differential phase	DP					0.5	deg.
Error rate	E _R	F _C = 250 MSPS F _{IN} = 62.499 MHz V_{IN} = 2 Vp-p tpw1 = 3.0 ns tpwo = 1.0 ns Error Threshold: 32 LSB				10^{-8}	times/ sample

(*2) Source impedance = 50 Ω .

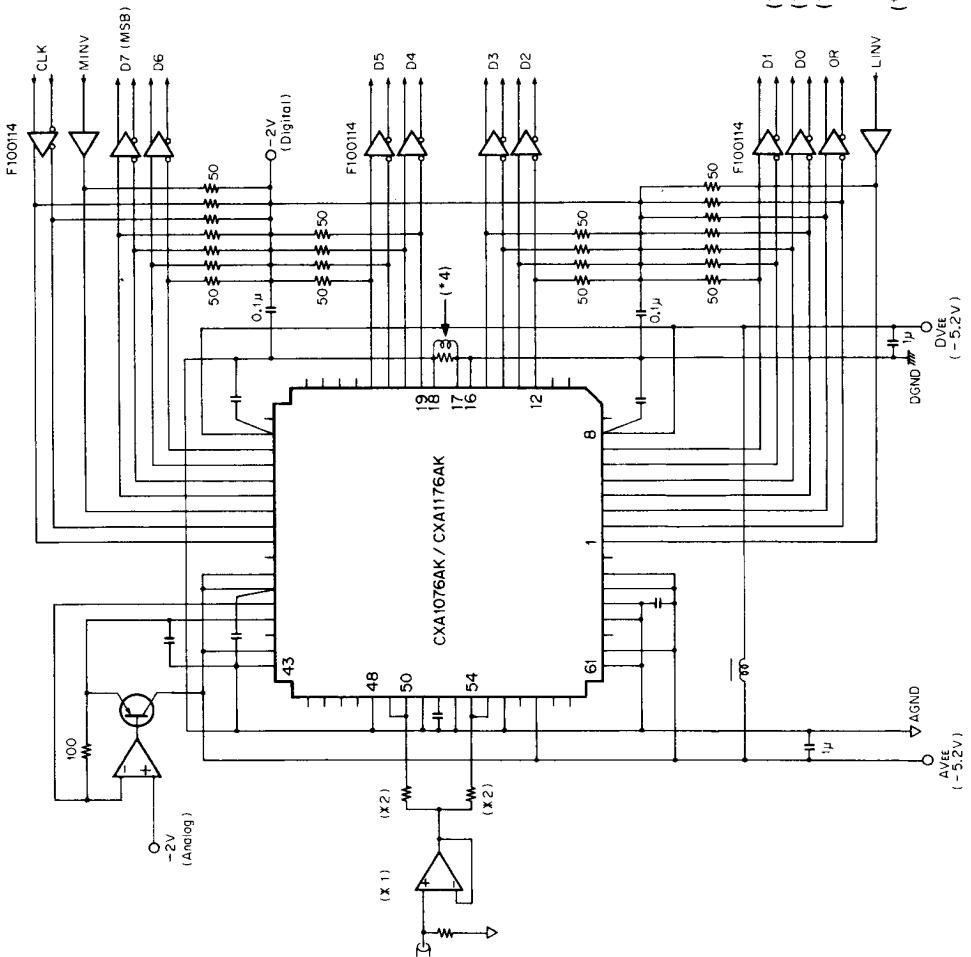
Application Circuit

Fig. 3

Notes on Application

- 1) AGND, DGND, AV_{EE} and DV_{EE} planes on a PCB should be designed to make those impedance small for the noise suppression benefits. Those planes should be made as wide as possible on the PCB with at least double layer metal patterns.
- 2) It is recommended to separate the analog and digital V_{EE} on the PCB patterns to make reduce a noise contamination from digital system to analog system.
- 3) If separate V_{EE} and GND are used, it is recommended to connect the digital and analog planes by a core inductor with good frequency characteristics to avoid the DC voltage difference between analog and digital planes.
The DC voltage difference between AGND and DGND degrades performance and a continual voltage difference between AV_{EE} and DV_{EE} may cause a destruction of the device.
- 4) The analog and analog power supply pins should be bypassed as close to the device as possible to their respective grounds with at least a 10 nF ceramic chip capacitor. A 1 μ F tantalum capacitor can also be used for low frequency bypassing.
- 5) Pin connections for the device should be made as short as possible. Using of a socket might degrade the performance because of an increasing of lead inductance. A possible compromise is to use AMP's socket 55159-2 (with heat sink).
- 6) A wide band drive amplifier with sufficient drivability and stable operation should be used to drive analog input pin. Comlinear's CLC231 may be used with adequate frequency compensation.
- 7) As the analog input impedance of the device is capacitive, the driving amplifier occasionally falls into unstable condition and oscillates locally. This instability can be prevented with a resistor inserted in series between the output pin of the amplifier and V_{IN} pins of the device. The resistor is to be selected from 2 to 20 Ω . Separate input for V_{IN} as shown in an application circuit (Fig. 3) may give a good result.
- 8) Digital output is delivered in complementary to make ease to interface in high speed operation. A 50 Ω termination at the endpoint of the wiring for both D_i and \bar{D}_i is recommended for noise suppression benefits.
- 9) V_{RTS} and V_{RBS} pins can be used as a sense for precise adjustment of reference voltage. Fig. 4 shows the adjustment scheme.

10) Internal current compensation circuit for the reference resistor is furnished in the device. This circuit compensates input bias current of the comparators to maintain the linearity over wide temperature range.

V_{RM} , the mid-point of the reference resistor can be used as a trimming pin for more accurate linearity as shown in Fig. 4.

V_{RT} , V_{RB} and V_{RM} should be bypassed to AGND with at least a 100 nF ceramic chip capacitor.

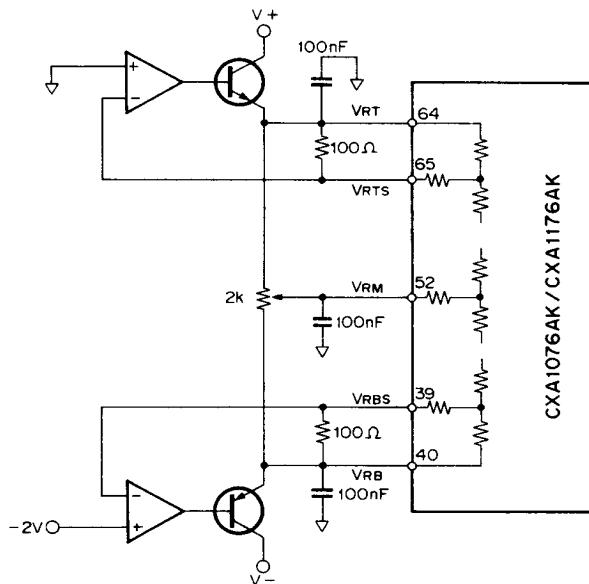
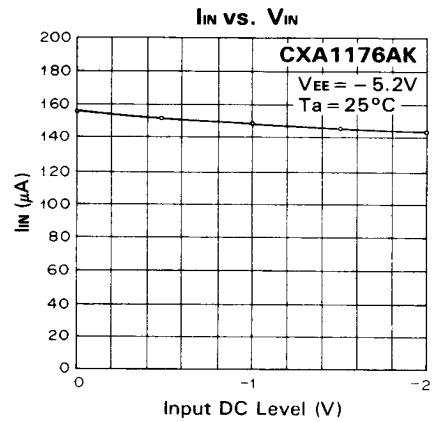
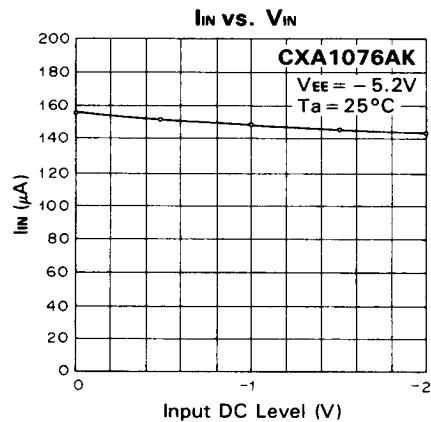
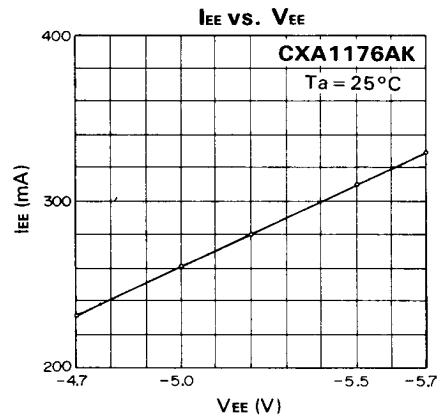
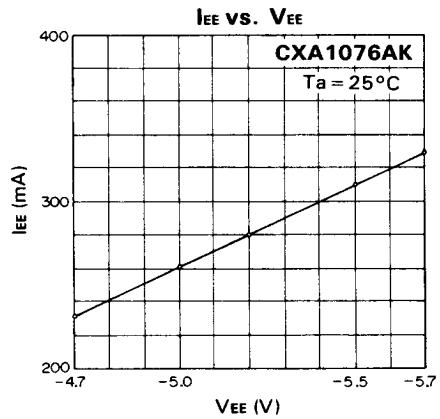
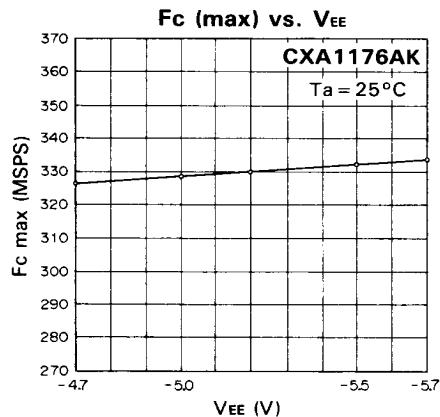
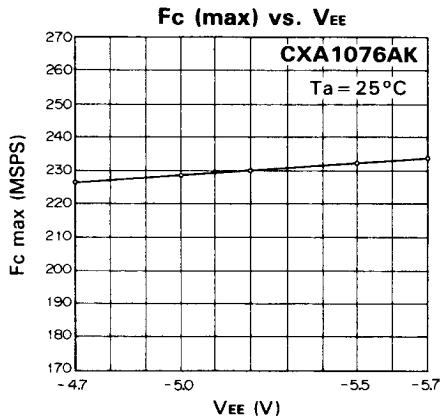
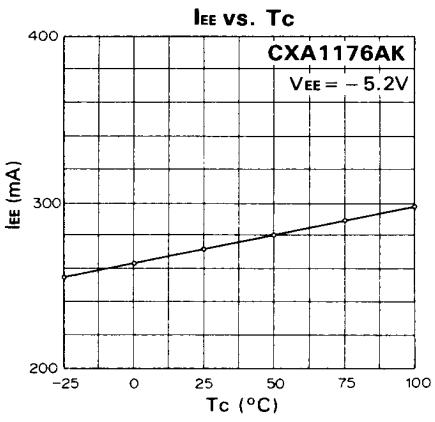
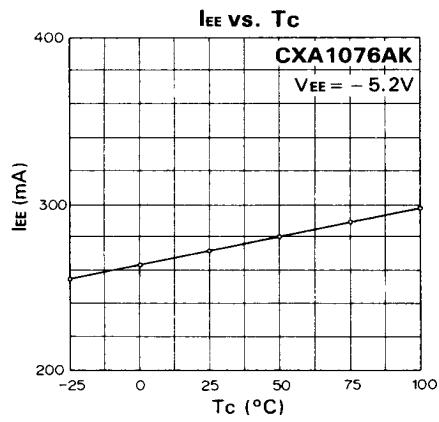
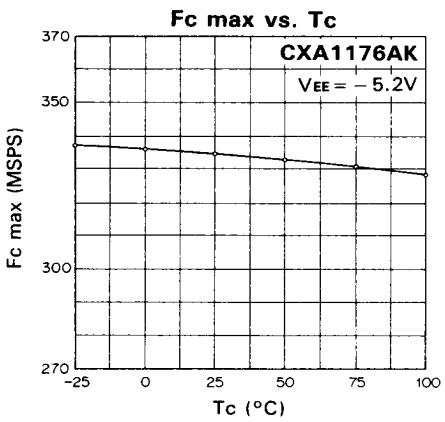
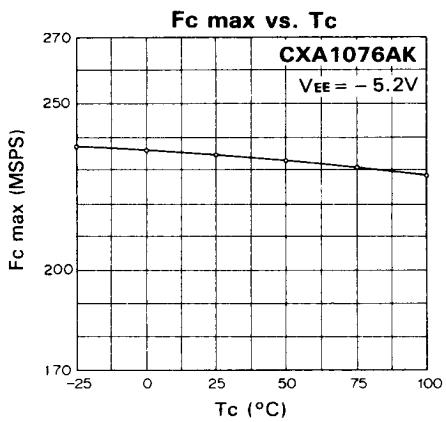
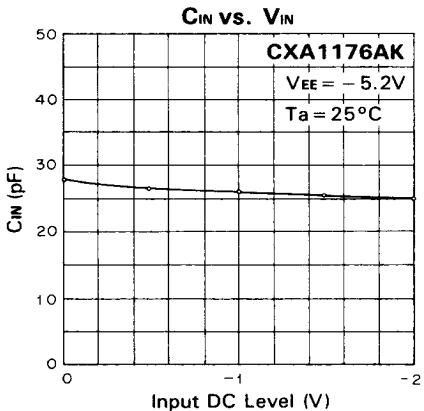
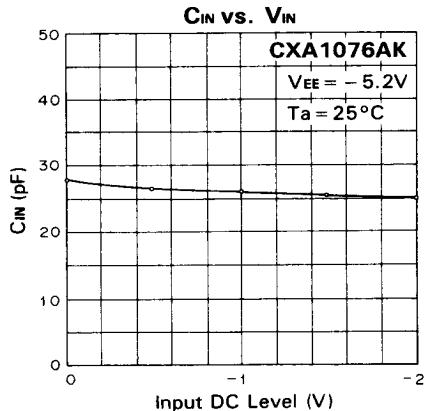


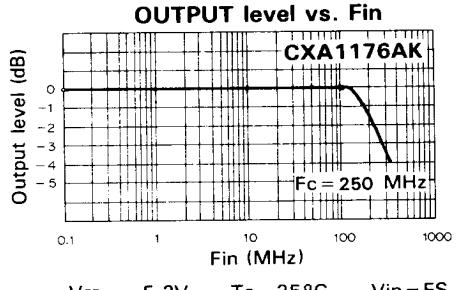
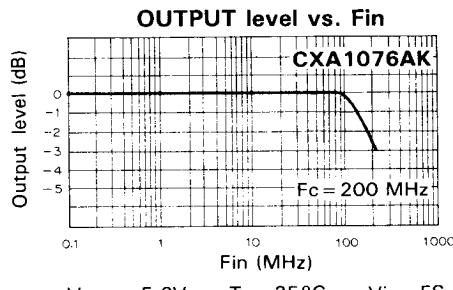
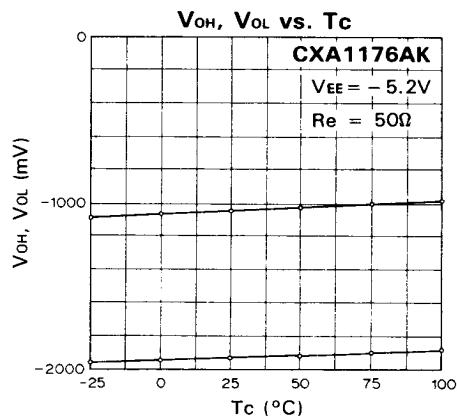
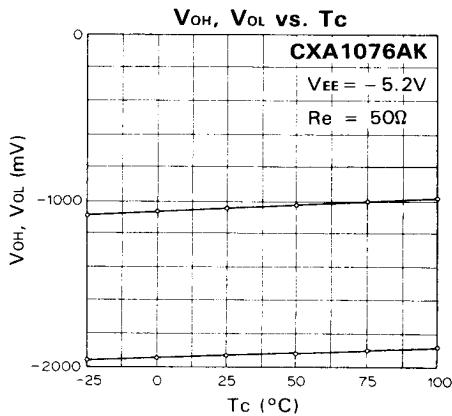
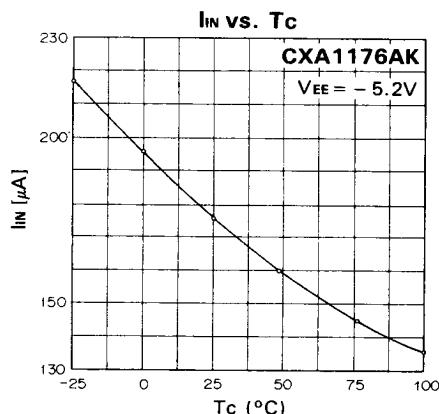
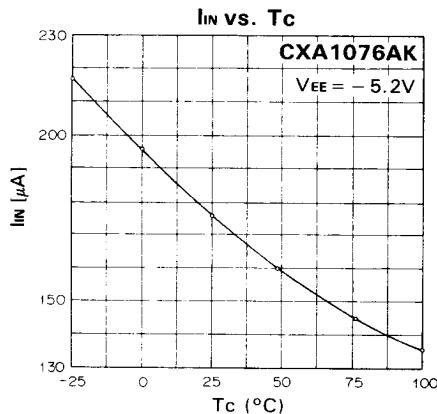
Fig. 4

11) OR and \overline{OR} output indicate that the input signal exceeds positive input range. MINV and LINV are not effective to the polarity of OR and \overline{OR} (Refer to the output format).

12) Pin 18 should be tied with AGND pins, not with system digital GND. Small resistor (approx. 1 ohm) and inductance 0.22 μ H having small resistance are recommended to use between pin 17 and 18. See "Application Circuit".





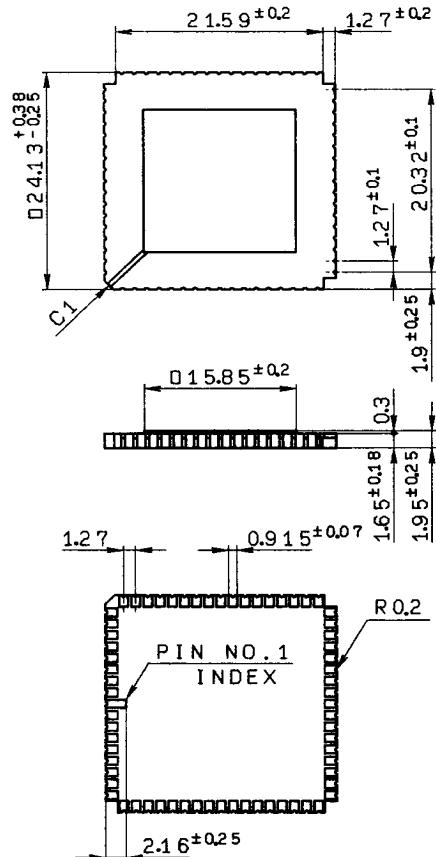


Preliminary

Preliminary

Package Outline Unit: mm

68 pin LCC (Ceramic) 3.7 g



LCC-68C-01